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Docket No.
90065.99R272 (17732.6323)

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

Applicant:	Jifa Hao,) Examiner:
) O. Nadav
Serial No.:	09/654,845)
) Art Unit:
Filed:	September 1, 2000) 2811
)
For:	POWER SEMICONDUCTOR DEVICE WITH HIGH)
	AVALANCE CAPABILITY AND PROCESS)
	FOR FORMING SAME)

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RESPONSE TO RESTRICTION REQUIREMENT

Honorable Commissioner of Patents and Trademarks
Washington, D.C. 20231

Dear Sir:

In response to the restriction requirement mailed by the U. S. Patent and Trademark Office on December 4, 2001, Applicants elect to prosecute the Group I claims (claims 1-17), drawn to a semiconductor device, without traverse.

Respectfully submitted,

1/4/02
Date

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